

Silicon PNP Power Transistors

2SA839

DESCRIPTION

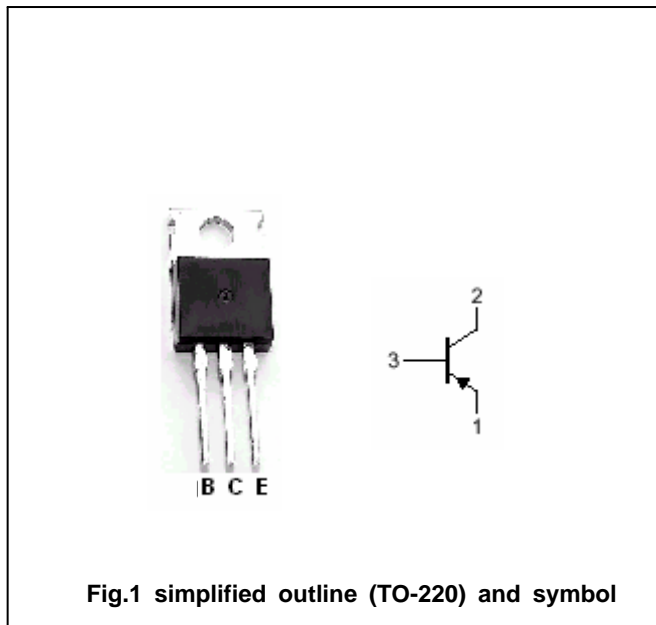
- With TO-220 package
- Complement to type 2SC1669
- High breakdown voltage

APPLICATIONS

- Audio power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_E	Emitter current		1.5	A
P_C	Collector power dissipation	$T_C=25$	25	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA, I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A; I _B =-50mA			-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-0.5A; V _{CE} =-10V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-10V	40		240	
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-10V	20			
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		100		pF
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V		6		MHz

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

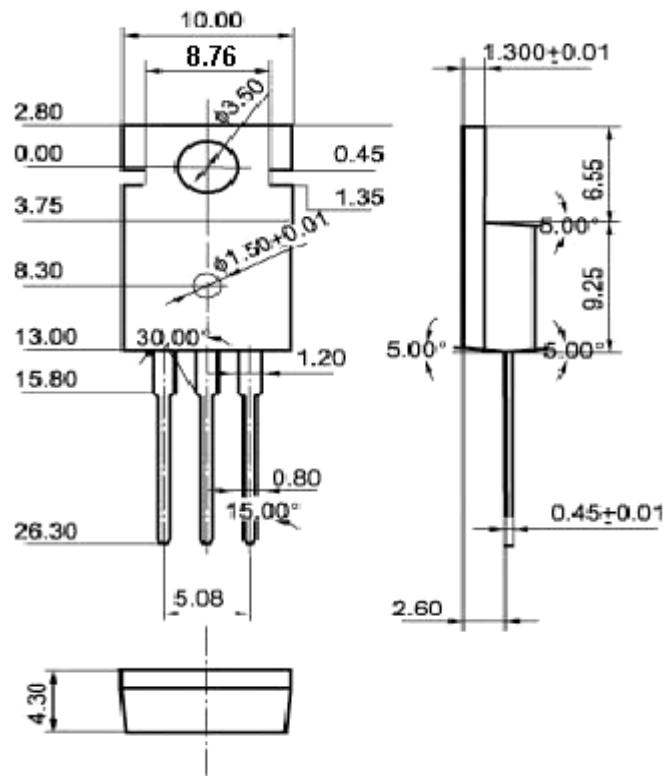


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)